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May 2017

## FODM3011, FODM3012, FODM3022, FODM3023, FODM3052, FODM3053 4-Pin Full Pitch Mini-Flat Package Random-Phase Triac Driver Output Optocouplers

## Features

- Compact 4-pin Surface Mount Package (2.4 mm Maximum Standoff Height)
- Peak Blocking Voltage
  - 250V (FODM301X)
  - 400V (FODM302X)
  - 600V (FODM305X)
- Safety and Regulatory Approvals:
  - UL1577, 3,750 VAC<sub>RMS</sub> for 1 Minute
  - DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage

## Applications

- Industrial Controls
- Traffic Lights
- Vending Machines
- Solid State Relay
- Lamp Ballasts
- Solenoid/Valve Controls
- Static AC Power Switch
- Incandescent Lamp Dimmers
- Motor Control

## Description

The FODM301X, FODM302X, and FODM305X series consists of a GaAs infrared emitting diode driving a silicon bilateral switch housed in a compact 4-pin miniflat package. The lead pitch is 2.54 mm. They are designed for interfacing between electronic controls and power triacs to control resistive and inductive loads for 115 V/240 V operations.



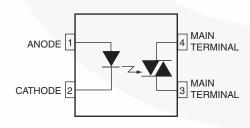


Figure 1. Functional Schematic

## Package Outlines

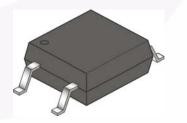


Figure 2. Package Outlines

## Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–111
Climatic Classification		40/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	$V_{PR} \begin{cases} Input-to-Output Test Voltage, Method A, V_{IORM} x 1.6 = V_{PR}, \\ Type and Sample Test with t_m = 10 s, Partial Discharge < 5 pC \\ Input-to-Output Test Voltage, Method B, V_{IORM} x 1.875 = V_{PR}, \\ 100\% Production Test with t_m = 1 s, Partial Discharge < 5 pC \\ \end{cases}$		V <sub>peak</sub>
<sup>v</sup> PR			V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	565	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥ 5	mm
	External Clearance	≥ 5	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
Τ <sub>S</sub>	Case Temperature <sup>(1)</sup>	150	°C
I <sub>S,INPUT</sub>	Input Current <sup>(1)</sup>	200	mA
P <sub>S,OUTPUT</sub>	Output Power <sup>(1)</sup>	300	mW
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , $V_{IO}$ = 500 $V^{(1)}$	> 10 <sup>9</sup>	Ω

#### Note:

1. Safety limit values - maximum values allowed in the event of a failure.

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Paramete	r	Value	Unit
T <sub>STG</sub>	Storage Temperature		-55 to +150	°C
T <sub>OPR</sub>	Operating Temperature		-40 to +100	°C
Τ <sub>J</sub>	Junction Temperature		-40 to +125	°C
T <sub>SOL</sub>	Lead Solder Temperature		260 for 10 sec	°C
EMITTER	·			
I <sub>F</sub> (avg)	Continuous Forward Current		60	mA
l <sub>F</sub> (pk)	Peak Forward Current (1 µs pulse, 300 p	ps.)	1	А
V <sub>R</sub>	Reverse Input Voltage		3	V
P <sub>D</sub>	Power Dissipation (No derating required of	over operating temp. range)	100	mW
DETECTOR	·			
I <sub>T(RMS)</sub>	On-State RMS Current		70	mA (RMS)
		FODM3011, FODM3012	250	
V <sub>DRM</sub>	Off-State Output Terminal Voltage	FODM3022, FODM3023	400	V
		FODM3052, FODM3053	600	
P <sub>D</sub>	Power Dissipation (No derating required of	over operating temp. range)	300	mW

## **Electrical Characteristics**

 $T_A = 25^{\circ}C$  unless otherwise specified.

#### **Individual Component Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Тур.	Max.	Unit
EMITTER							
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 10 mA	All		1.20	1.50	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 3 V, T <sub>A</sub> = 25°C	All		0.01	100	μA
DETECTOR							
I <sub>DRM</sub>	Peak Blocking Current Either Direction	Rated V <sub>DRM</sub> , $I_F = 0^{(2)}$	All		2	100	nA
dV/dt	Critical Rate of Rise of Off-State Voltage	I <sub>F</sub> = 0 (Figure 8) <sup>(3)</sup>	FODM3011, FODM3012, FODM3022, FODM3023		10		V/µs
			FODM3052, FODM3053	1,000			

Notes:

2. Test voltage must be applied within dv/dt rating.

3. This is static dv/dt. See Figure 1 for test circuit Commutating dv/dt is function of the load-driving thyristor(s) only.

#### **Transfer Characteristics**

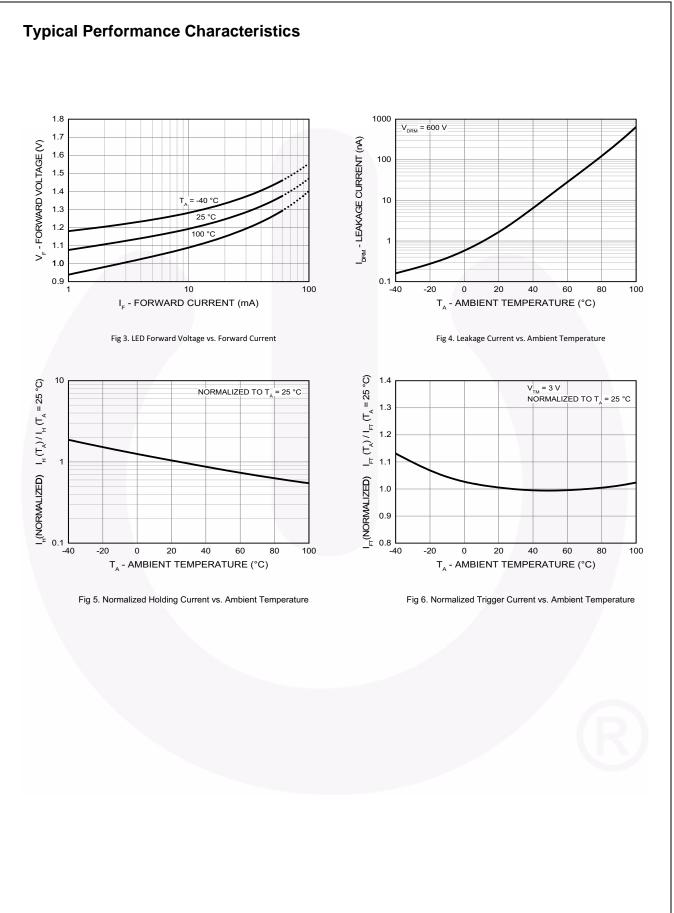
Symbol	Parameter	Test Conditions	Device	Min.	Тур.	Max.	Unit
		Main Terminal	FODM3011, FODM3022, FODM3052			10	mA
I <sub>T</sub> LED Trigger Cu			FODM3012, FODM3023, FODM3053			5	1 IIIA
Ι <sub>Η</sub>	Holding Current, Either Direction		All		450		μA
V <sub>TM</sub>	Peak On-State Voltage Either Direction	I <sub>TM</sub> = 100 mA peak	All		2.2	3	V

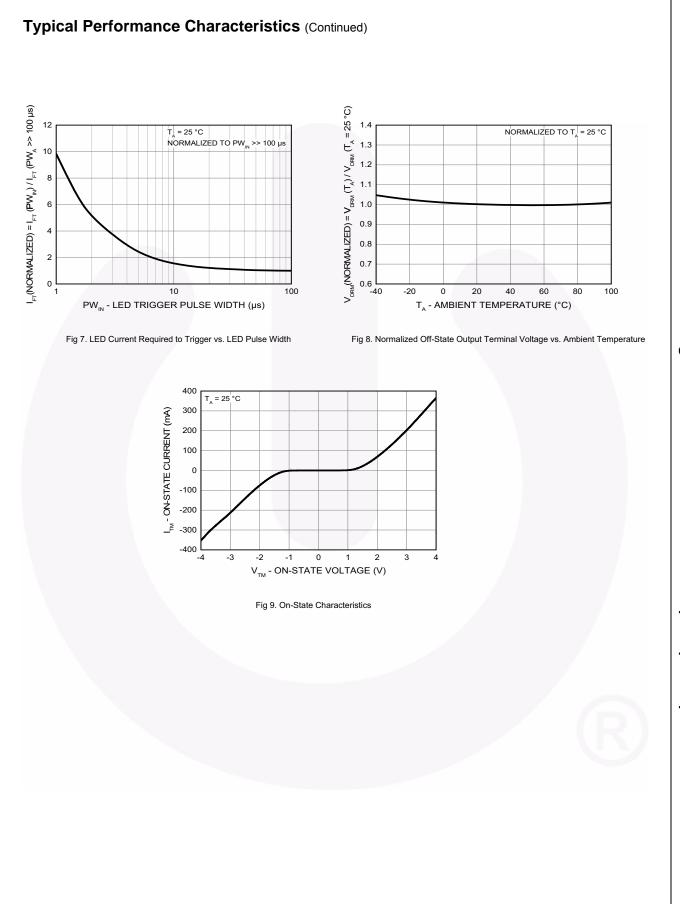
Notes:

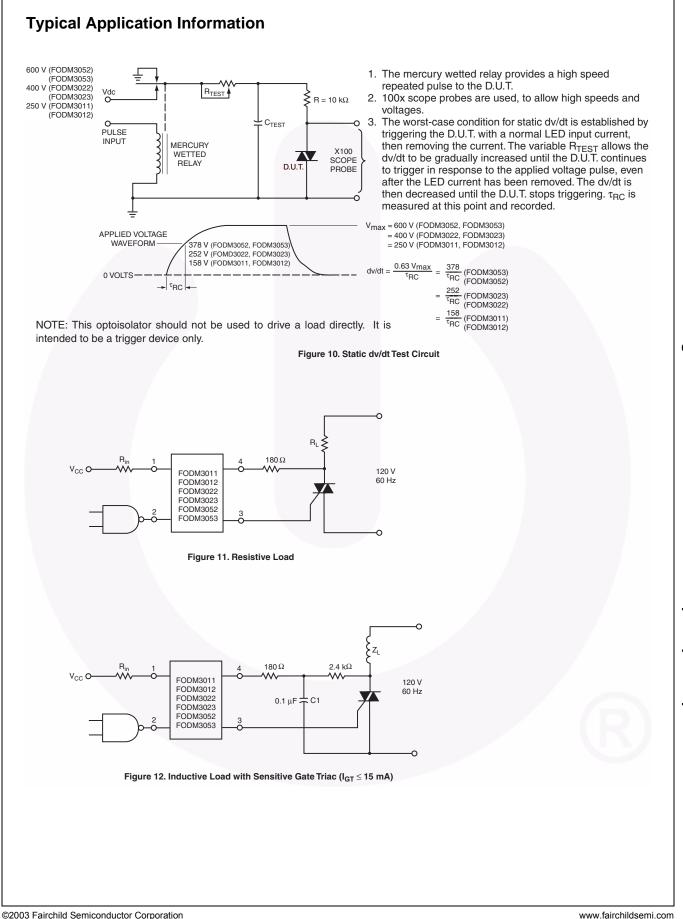
4. All devices are guaranteed to trigger at an I<sub>F</sub> value of less than or equal to the max I<sub>FT</sub> specification. For optimum operation over temperature and lifetime of the device, the LED should be biased with an I<sub>F</sub> that is at least 50% higher than the maximum I<sub>FT</sub> specification. The I<sub>FT</sub> should not exceed the absolute maximum rating of 60 mA. Example: For FODM0353M, the minimum I<sub>F</sub> bias should be 5 mA x 150% = 7.5 mA

#### **Isolation Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Тур.	Max.	Unit
V <sub>ISO</sub>	Steady State Isolation Voltage	1 Minute, R.H. = 40% to 60%	All	3,750			VAC <sub>RMS</sub>

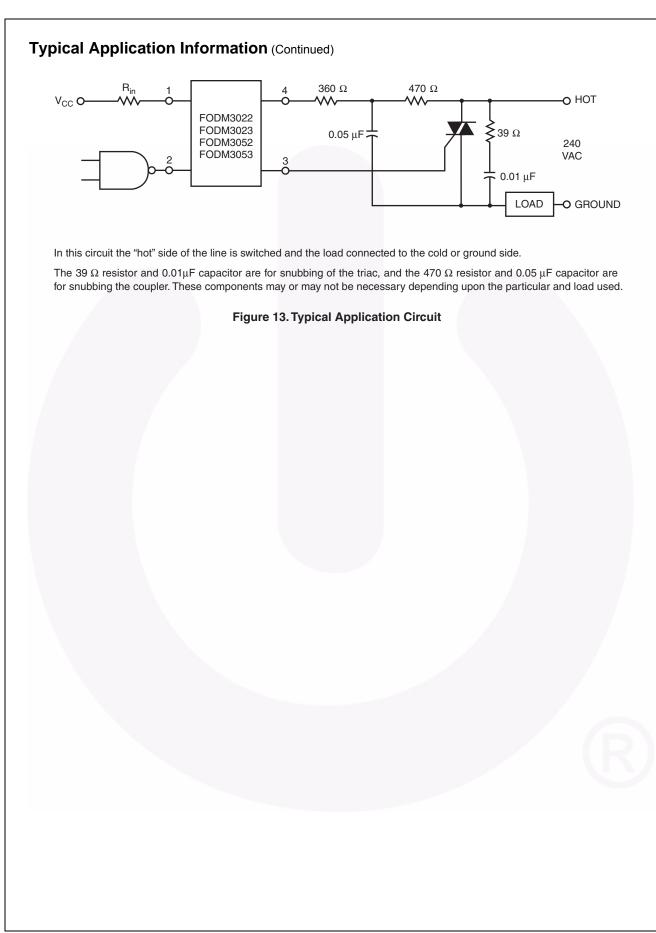


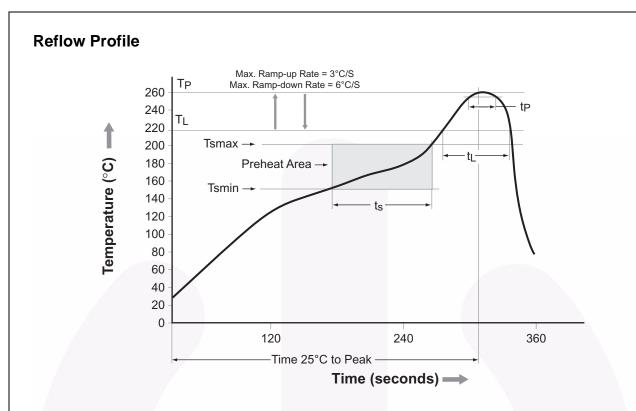




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Profile Freature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60–150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

## **Ordering Information**

Part Number	Package	Packing Method
FODM3011	Full Pitch Mini-Flat 4-Pin	Tube (100 units)
FODM3011R2	Full Pitch Mini-Flat 4-Pin	Tape and Reel (2500 Units)
FODM3011V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 Units)
FODM3011R2V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (2500 Units)

#### Note:

The product orderable part number system listed in this table also applies to the FODM3012, FODM3022, FODM3023, FODM3052, and FODM3053 products.

## **Marking Information**

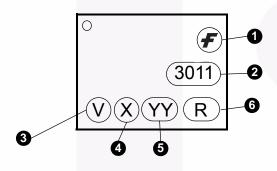
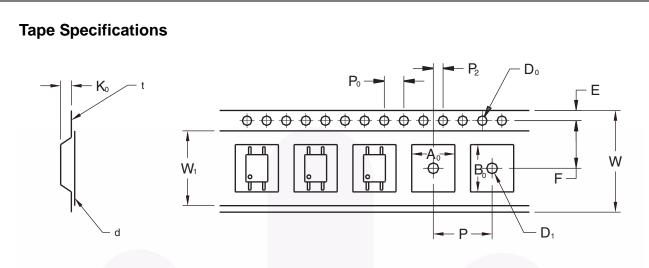


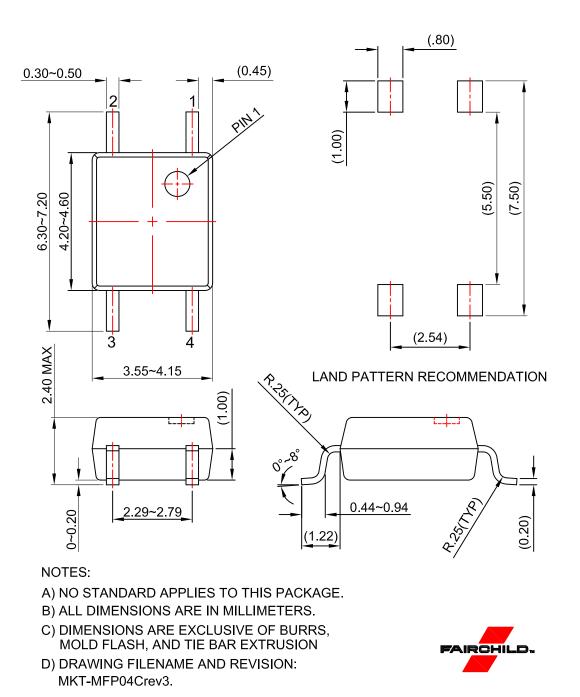
Figure 14. Top Mark

#### Table 1. Top Mark Definitions

1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "6"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code



	_	
		2.54 Pitch
Description	Symbol	Dimensions
Tape Width	W	12.00±0.4
Tape Thickness	t	0.35±0.02
Sprocket Hole Pitch	Po	4.00±0.20
Sprocket Hole Dia.	Do	1.55±0.20
Sprocket Hole Location	E	1.75±0.20
Pocket Location	F	5.50±0.20
	P <sub>2</sub>	2.00±0.20
Pocket Pitch	P	8.00±0.20
Pocket Dimension	A <sub>0</sub>	4.75±0.20
	B <sub>0</sub>	7.30±0.20
	K <sub>0</sub>	2.30±0.20
Pocket Hole Dia.	D <sub>1</sub>	1.55±0.20
Cover Tape Width	W1	9.20
Cover Tape Thickness	d	0.065±0.02
Max. Component Rotation or Tilt		20° max
Devices Per Reel		2500
Reel Diameter		330 mm (13")



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